

Isc N-Channel MOSFET Transistor

STP100N8F6

• FEATURES

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

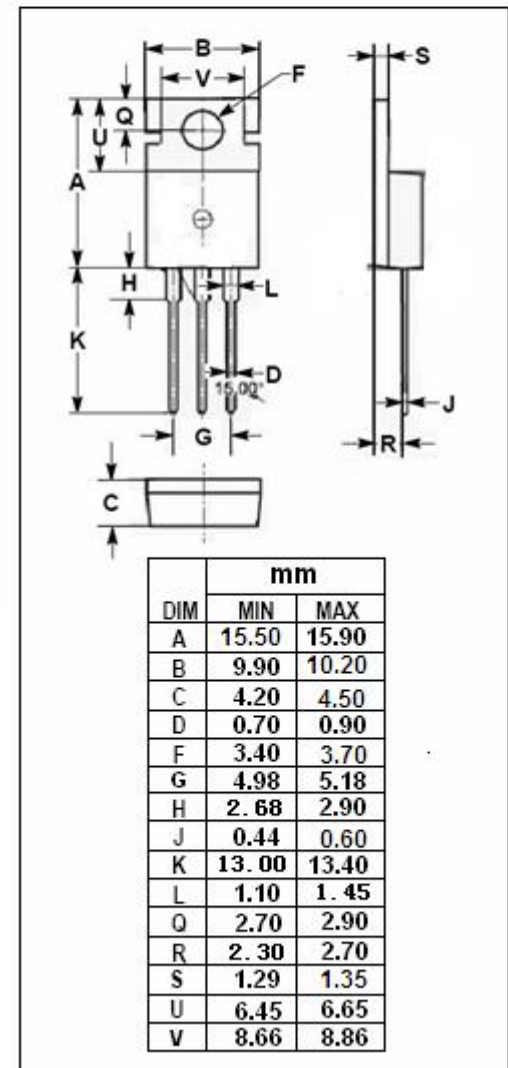
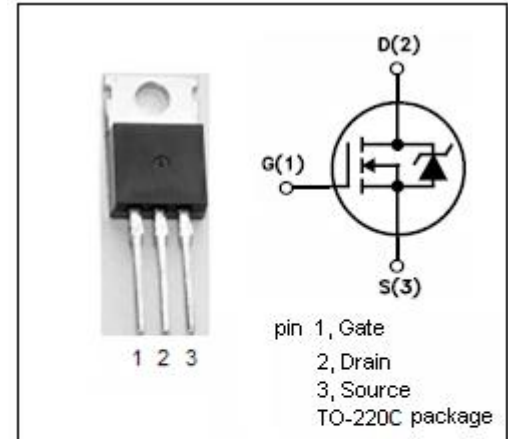
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	100 70	A
I_{DM}	Drain Current-Single Pulsed	400	A
P_D	Total Dissipation	176	W
T_j	Operating Junction Temperature	-55~175	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~175	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.85	$^{\circ}\text{C}/\text{W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62.5	$^{\circ}\text{C}/\text{W}$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	80			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =±20V; I _D =0.25mA	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =50A		8	9	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 80V; V _{GS} = 0V; T _J =25°C T _J =125°C			1 100	μA
V _{SDF}	Diode forward voltage	I _{SD} =100A, V _{GS} = 0 V			1.2	V